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### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

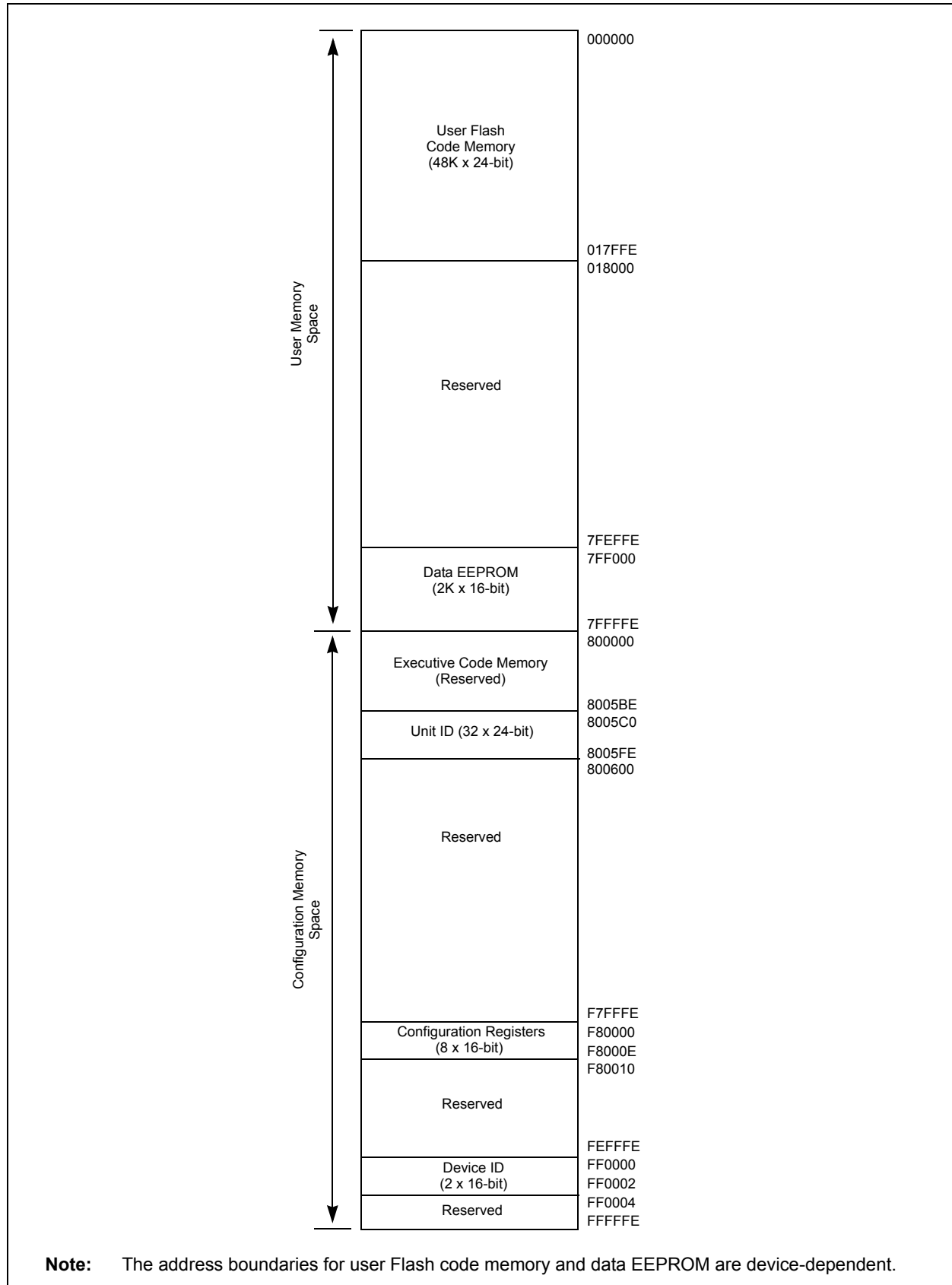
### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	20 MIPS
Connectivity	I <sup>2</sup> C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	20
Program Memory Size	24KB (8K x 24)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	28-SOIC (0.295", 7.50mm Width)
Supplier Device Package	28-SOIC
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/dspic30f3013t-20e-so">https://www.e-xfl.com/product-detail/microchip-technology/dspic30f3013t-20e-so</a>

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FIGURE 2-2: PROGRAM MEMORY MAP



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## 5.0 DEVICE PROGRAMMING

### 5.1 Overview of the Programming Process

Once the programming executive has been verified in memory (or loaded if not present), the dsPIC30F can be programmed using the command set shown in [Table 5-1](#). A detailed description for each command is provided in [Section 8.0 “Programming Executive Commands”](#).

**TABLE 5-1: COMMAND SET SUMMARY**

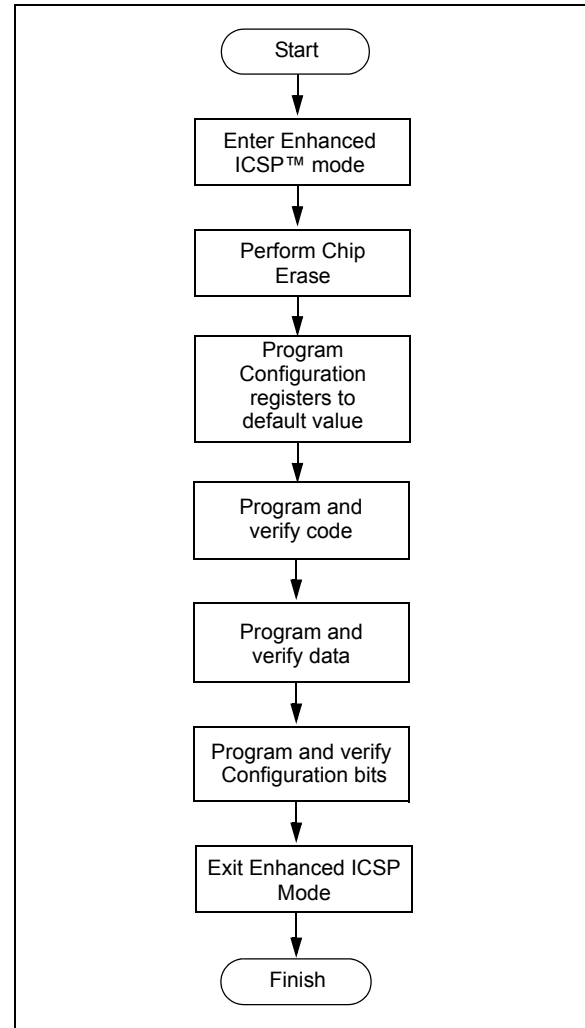
Command	Description
SCHECK	Sanity check
READD	Read data EEPROM, Configuration registers and device ID
READP	Read code memory
PROGD	Program one row of data EEPROM and verify
PROGP	Program one row of code memory and verify
PROGC	Program Configuration bits and verify
ERASEB	Bulk Erase, or erase by segment
ERASED	Erase data EEPROM
ERASEP	Erase code memory
QBLANK	Query if the code memory and data EEPROM are blank
QVER	Query the software version

A high-level overview of the programming process is illustrated in [Figure 5-1](#). The process begins by entering Enhanced ICSP mode. The chip is then bulk erased, which clears all memory to ‘1’ and allows the device to be programmed. The Chip Erase is verified before programming begins. Next, the code memory, data Flash and Configuration bits are programmed. As these memories are programmed, they are each verified to ensure that programming was successful. If no errors are detected, the programming is complete and Enhanced ICSP mode is exited. If any of the verifications fail, the procedure should be repeated, starting from the Chip Erase.

If Advanced Security features are enabled, then individual Segment Erase operations need to be performed, based on user selections (i.e., based on the specific needs of the user application). The specific operations that are used typically depend on the order in which various segments need to be programmed for a given application or system.

[Section 5.2 “Entering Enhanced ICSP Mode”](#) through [Section 5.8 “Exiting Enhanced ICSP Mode”](#) describe the programming process in detail.

**FIGURE 5-1: PROGRAMMING FLOW**



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**TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015 (CONTINUED)**

Bit Field	Register	Description
FPR<4:0>	FOSC	<b>Alternate Oscillator Mode (when FOS&lt;2:0&gt; = 011b)</b> 1xxxx = Reserved (do not use) 0111x = Reserved (do not use) 01101 = Reserved (do not use) 01100 = ECIO – External clock. OSC2 pin is I/O 01011 = EC – External clock. OSC2 pin is system clock output (Fosc/4) 01010 = Reserved (do not use) 01001 = ERC – External RC oscillator. OSC2 pin is system clock output (Fosc/4) 01000 = ERCIO – External RC oscillator. OSC2 pin is I/O 00111 = Reserved (do not use) 00110 = Reserved (do not use) 00101 = Reserved (do not use) 00100 = XT – XT crystal oscillator (4 MHz-10 MHz crystal) 00010 = HS – HS crystal oscillator (10 MHz-25 MHz crystal) 00001 = Reserved (do not use) 00000 = XTL – XTL crystal oscillator (200 kHz-4 MHz crystal)

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**TABLE 5-7: CONFIGURATION BITS DESCRIPTION (CONTINUED)**

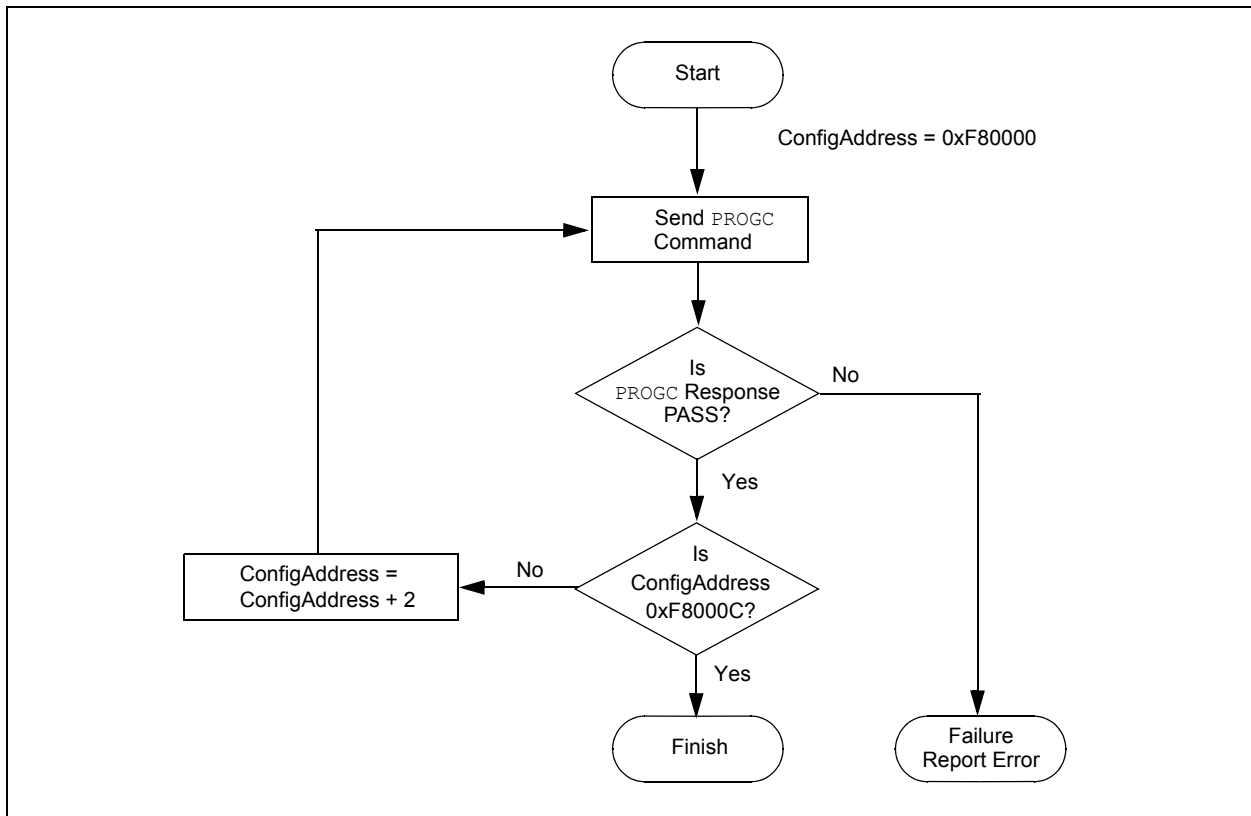
Bit Field	Register	Description
SSS<2:0>	FSS	<b>Secure Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)</b> 111 = No Secure Segment 110 = Standard security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 101 = Standard security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 100 = Standard security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF] 011 = No Secure Segment 010 = High security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 001 = High security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 000 = High security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF]
SWRP	FSS	<b>Secure Segment Program Memory Write Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)</b> 1 = Secure Segment program memory is not write-protected 0 = Secure program memory is write-protected
GSS<1:0>	FGS	<b>General Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)</b> 11 = Code protection is disabled 10 = Standard security code protection is enabled 0x = High security code protection is enabled
GCP	FGS	<b>General Segment Program Memory Code Protection (present in all devices except dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)</b> 1 = General Segment program memory is not code-protected 0 = General Segment program memory is code-protected
GWRP	FGS	<b>General Segment Program Memory Write Protection</b> 1 = General Segment program memory is not write-protected 0 = General Segment program memory is write-protected
BKBUG	FICD	<b>Debugger/Emulator Enable</b> 1 = Device will reset into Operational mode 0 = Device will reset into Debug/Emulation mode
COE	FICD	<b>Debugger/Emulator Enable</b> 1 = Device will reset into Operational mode 0 = Device will reset into Clip-on Emulation mode
ICS<1:0>	FICD	<b>ICD Communication Channel Select</b> 11 = Communicate on PGC/EMUC and PGD/EMUD 10 = Communicate on EMUC1 and EMUD1 01 = Communicate on EMUC2 and EMUD2 00 = Communicate on EMUC3 and EMUD3
RESERVED	FBS, FSS, FGS	<b>Reserved (read as '1', write as '1')</b>
—	All	<b>Unimplemented (read as '0', write as '0')</b>

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## 5.8 Exiting Enhanced ICSP Mode

The Enhanced ICSP mode is exited by removing power from the device or bringing MCLR to V<sub>IL</sub>. When normal user mode is next entered, the program that was stored using Enhanced ICSP will execute.

**FIGURE 5-5: CONFIGURATION BIT PROGRAMMING FLOW**



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## 8.0 PROGRAMMING EXECUTIVE COMMANDS

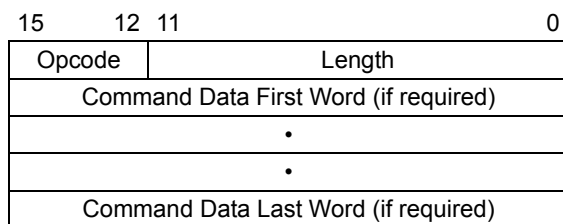
### 8.1 Command Set

The programming executive command set is shown in [Table 8-1](#). This table contains the opcode, mnemonic, length, time out and description for each command. Functional details on each command are provided in the command descriptions (see [Section 8.5 “Command Descriptions”](#)).

### 8.2 Command Format

All programming executive commands have a general format consisting of a 16-bit header and any required data for the command (see [Figure 8-1](#)). The 16-bit header consists of a 4-bit opcode field, which is used to identify the command, followed by a 12-bit command length field.

**FIGURE 8-1: COMMAND FORMAT**



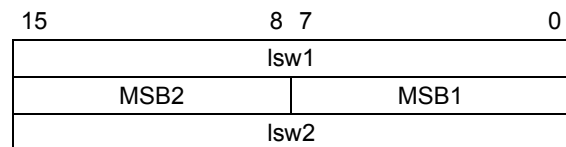
The command opcode must match one of those in the command set. Any command that is received which does not match the list in [Table 8-1](#) will return a “NACK” response (see [Section 9.2.1 “Opcode Field”](#)).

The command length is represented in 16-bit words since the SPI operates in 16-bit mode. The programming executive uses the Command Length field to determine the number of words to read from the SPI port. If the value of this field is incorrect, the command will not be properly received by the programming executive.

### 8.3 Packed Data Format

When 24-bit instruction words are transferred across the 16-bit SPI interface, they are packed to conserve space using the format shown in [Figure 8-2](#). This format minimizes traffic over the SPI and provides the programming executive with data that is properly aligned for performing table write operations.

**FIGURE 8-2: PACKED INSTRUCTION WORD FORMAT**



lswx: Least significant 16 bits of instruction word

MSBx: Most Significant Byte of instruction word

**Note:** When the number of instruction words transferred is odd, MSB2 is zero and lsw2 cannot be transmitted.

### 8.4 Programming Executive Error Handling

The programming executive will “NACK” all unsupported commands. Additionally, due to the memory constraints of the programming executive, no checking is performed on the data contained in the Programmer command. It is the responsibility of the programmer to command the programming executive with valid command arguments, or the programming operation may fail. Additional information on error handling is provided in [Section 9.2.3 “QE\\_Code Field”](#).

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## 8.5.3 READP COMMAND

15	12	11	8	7	0
Opcode		Length			
N					
Reserved			Addr_MSB		
Addr_LS					

Field	Description
Opcode	0x2
Length	0x4
N	Number of 24-bit instructions to read (max of 32768)
Reserved	0x0
Addr_MSB	MSB of 24-bit source address
Addr_LS	LS 16 bits of 24-bit source address

The **READP** command instructs the programming executive to read N 24-bit words of code memory starting from the 24-bit address specified by Addr\_MSB and Addr\_LS. This command can only be used to read 24-bit data. All data returned in response to this command uses the packed data format described in [Section 8.3 “Packed Data Format”](#).

### Expected Response (2 + 3 \* N/2 words for N even):

0x1200

2 + 3 \* N/2

Least significant program memory word 1

...

Least significant data word N

### Expected Response (4 + 3 \* (N – 1)/2 words for N odd):

0x1200

4 + 3 \* (N – 1)/2

Least significant program memory word 1

...

MSB of program memory word N (zero padded)

**Note:** Reading unimplemented memory will cause the programming executive to reset.

## 8.5.4 PROGD COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
D_1					
D_2					
...					
D_16					

Field	Description
Opcode	0x4
Length	0x13
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
D_1	16-bit data word 1
D_2	16-bit data word 2
...	16-bit data words 3 through 15
D_16	16-bit data word 16

The **PROGD** command instructs the programming executive to program one row of data EEPROM. The data to be programmed is specified by the 16 data words (D\_1, D\_2,..., D\_16) and is programmed to the destination address specified by Addr\_MSB and Addr\_LSB. The destination address should be a multiple of 0x20.

Once the row of data EEPROM has been programmed, the programming executive verifies the programmed data against the data in the command.

### Expected Response (2 words):

0x1400

0x0002

**Note:** Refer to [Table 5-3](#) for data EEPROM size information.



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## 8.5.5 PROGP COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
D_1					
D_2					
...					
D_N					

Field	Description
Opcode	0x5
Length	0x33
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
D_1	16-bit data word 1
D_2	16-bit data word 2
...	16-bit data word 3 through 47
D_48	16-bit data word 48

The **PROGP** command instructs the programming executive to program one row of code memory (32 instruction words) to the specified memory address. Programming begins with the row address specified in the command. The destination address should be a multiple of 0x40.

The data to program to memory, located in command words D\_1 through D\_48, must be arranged using the packed instruction word format shown in [Figure 8-2](#).

After all data has been programmed to code memory, the programming executive verifies the programmed data against the data in the command.

### Expected Response (2 words):

0x1500  
0x0002

**Note:** Refer to [Table 5-2](#) for code memory size information.

## 8.5.6 PROGC COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
Data					

Field	Description
Opcode	0x6
Length	0x4
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
Data	Data to program

The **PROGC** command programs data to the specified Configuration register and verifies the programming. Configuration registers are 16 bits wide, and this command allows one Configuration register to be programmed.

### Expected Response (2 words):

0x1600  
0x0002

**Note:** This command can only be used for programming Configuration registers.

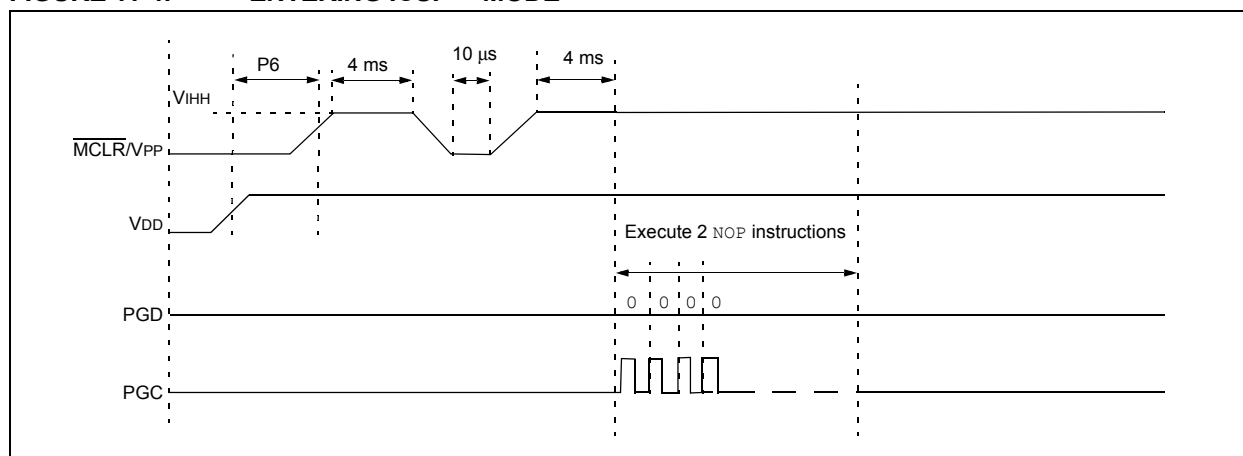
# dsPIC30F Flash Programming Specification

## 11.3 Entering ICSP Mode

The ICSP mode is entered by holding PGC and PGD low, raising MCLR/VPP to VIH (high voltage), and then performing additional steps as illustrated in [Figure 11-4](#).

- Note 1:** The sequence that places the device into ICSP mode places all unused I/O pins to the high-impedance state.
- 2:** Once ICSP mode is entered, the PC is set to 0x0 (the Reset vector).
- 3:** Before leaving the Reset vector, execute two GOTO instructions, followed by a single NOP instruction must be executed.

**FIGURE 11-4: ENTERING ICSP™ MODE**



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## 11.6 Erasing Program Memory in Low-Voltage Systems

The procedure for erasing program memory (all code memory and data memory) in low-voltage systems (with VDD between 2.5 volts and 4.5 volts) is quite different than the procedure for erasing program memory in normal-voltage systems. Instead of using a Bulk Erase operation, each region of memory must be individually erased by row. Namely, all of the code memory, executive memory and data memory must be erased one row at a time. This procedure is detailed in [Table 11-5](#).

Due to security restrictions, the FBS, FSS and FGS register cannot be erased in low-voltage systems. Once any bits in the FGS register are programmed to '0', they can only be set back to '1' by performing a Bulk Erase in a normal-voltage system. Alternatively, a Segment Erase operation can be performed instead of a Bulk Erase.

Normal-voltage systems can also be used to erase program memory as shown in [Table 11-5](#). However, since this method is more time-consuming and does not clear the code-protect bits, it is not recommended.

**Note:** Program memory must be erased before writing any data to program memory.

**TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY (EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Initialize NVMADR and NVMADRU to erase code memory and initialize W7 for row address updates.</b>		
0000	EB0300	CLR W6
0000	883B16	MOV W6, NVMADR
0000	883B26	MOV W6, NVMADRU
0000	200407	MOV #0x40, W7
<b>Step 3: Set NVMCON to erase 1 row of code memory.</b>		
0000	24071A	MOV #0x4071, W10
0000	883B0A	MOV W10, NVMCON
<b>Step 4: Unlock the NVMCON to erase 1 row of code memory.</b>		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 5: Initiate the erase cycle.</b>		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P13a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP

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## 11.8 Writing Code Memory

The procedure for writing code memory is similar to the procedure for clearing the Configuration registers, except that 32 instruction words are programmed at a time. To facilitate this operation, working registers W0:W5 are used as temporary holding registers for the data to be programmed.

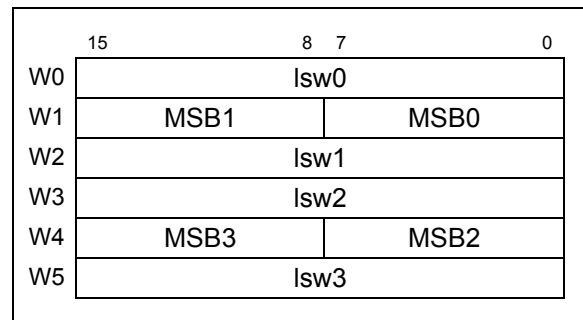
Table 11-8 shows the ICSP programming details, including the serial pattern with the ICSP command code, which must be transmitted Least Significant bit first using the PGC and PGD pins (see Figure 11-2). In Step 1, the Reset vector is exited. In Step 2, the NVMCON register is initialized for single-panel programming of code memory. In Step 3, the 24-bit starting destination address for programming is loaded into the TBLPAG register and W7 register. The upper byte of the starting destination address is stored to TBLPAG, while the lower 16 bits of the destination address are stored to W7.

To minimize the programming time, the same packed instruction format that the programming executive uses is utilized (Figure 8-2). In Step 4, four packed instruction words are stored to working registers W0:W5 using the MOV instruction and the read pointer W6 is initialized. The contents of W0:W5 holding the packed instruction word data is shown in Figure 11-4.

In Step 5, eight TBLWT instructions are used to copy the data from W0:W5 to the write latches of code memory. Since code memory is programmed 32 instruction words at a time, Steps 4 and 5 are repeated eight times to load all the write latches (Step 6).

After the write latches are loaded, programming is initiated by writing to the NVMKEY and NVMCON registers in Steps 7 and 8. In Step 9, the internal PC is reset to 0x100. This is a precautionary measure to prevent the PC from incrementing into unimplemented memory when large devices are being programmed. Lastly, in Step 10, Steps 2-9 are repeated until all of code memory is programmed.

**FIGURE 11-5: PACKED INSTRUCTION WORDS IN W0:W5**



**TABLE 11-8: SERIAL INSTRUCTION EXECUTION FOR WRITING CODE MEMORY**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Set the NVMCON to program 32 instruction words.</b>		
0000	24001A	MOV #0x4001, W10
0000	883B0A	MOV W10, NVMCON
<b>Step 3: Initialize the write pointer (W7) for TBLWT instruction.</b>		
0000	200xx0	MOV #<DestinationAddress23:16>, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx7	MOV #<DestinationAddress15:0>, W7
<b>Step 4: Initialize the read pointer (W6) and load W0:W5 with the next 4 instruction words to program.</b>		
0000	2xxxx0	MOV #<LSW0>, W0
0000	2xxxx1	MOV #<MSB1:MSB0>, W1
0000	2xxxx2	MOV #<LSW1>, W2
0000	2xxxx3	MOV #<LSW2>, W3
0000	2xxxx4	MOV #<MSB3:MSB2>, W4
0000	2xxxx5	MOV #<LSW3>, W5

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**TABLE 11-8: SERIAL INSTRUCTION EXECUTION FOR WRITING CODE MEMORY (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 5:</b> Set the read pointer (W6) and load the (next set of) write latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDDB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBE6B6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDDB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBE6B6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 6:</b> Repeat steps 4-5 eight times to load the write latches for 32 instructions.		
<b>Step 7:</b> Unlock the NVMCON for writing.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 8:</b> Initiate the write cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
<b>Step 9:</b> Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 10:</b> Repeat steps 2-9 until all code memory is programmed.		

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TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 7: Unlock the NVMCON for writing.</b>		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 8: Initiate the write cycle.</b>		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
<b>Step 9: Reset device internal PC.</b>		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 10: Repeat steps 2-9 until all data memory is programmed.</b>		

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## 11.10 Reading Code Memory

Reading from code memory is performed by executing a series of TBLRD instructions and clocking out the data using the REGOUT command. To ensure efficient execution and facilitate verification on the programmer, four instruction words are read from the device at a time.

Table 11-10 shows the ICSP programming details for reading code memory. In Step 1, the Reset vector is exited. In Step 2, the 24-bit starting source address for reading is loaded into the TBLPAG and W6 registers. The upper byte of the starting source address is stored to TBLPAG, while the lower 16 bits of the source address are stored to W6.

To minimize the reading time, the packed instruction word format that was utilized for writing is also used for reading (see Figure 11-5). In Step 3, the write pointer W7 is initialized, and four instruction words are read from code memory and stored to working registers W0:W5. In Step 4, the four instruction words are clocked out of the device from the VISI register using the REGOUT command. In Step 5, the internal PC is reset to 0x100, as a precautionary measure, to prevent the PC from incrementing into unimplemented memory when large devices are being read. Lastly, in Step 6, Steps 3-5 are repeated until the desired amount of code memory is read.

**TABLE 11-10: SERIAL INSTRUCTION EXECUTION FOR READING CODE MEMORY**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.</b>		
0000	200xx0	MOV #<SourceAddress23:16>, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx6	MOV #<SourceAddress15:0>, W6
<b>Step 3: Initialize the write pointer (W7) and store the next four locations of code memory to W0:W5.</b>		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA0BB6	TBLRDL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP

# dsPIC30F Flash Programming Specification

## 11.12 Reading Data Memory

The procedure for reading data memory is similar to that of reading code memory, except that 16-bit data words are read instead of 24-bit words. Since less data is read in each operation, only working registers W0:W3 are used as temporary holding registers for the data to be read.

Table 11-12 shows the ICSP programming details for reading data memory. Note that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data memory).

**TABLE 11-12: SERIAL INSTRUCTION EXECUTION FOR READING DATA MEMORY**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.</b>		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx6	MOV #<SourceAddress15:0>, W6
<b>Step 3: Initialize the write pointer (W7) and store the next four locations of code memory to W0:W5.</b>		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 4: Output W0:W5 using the VISI register and REGOUT command.</b>		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
<b>Step 5: Reset device internal PC.</b>		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 6: Repeat steps 3-5 until all desired data memory is read.</b>		



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**TABLE 12-1: PROGRAMMING THE PROGRAMMING EXECUTIVE (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 8:</b> Set the read pointer (W6) and load the (next four write) latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BEBBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BEBBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 9:</b> Repeat Steps 7-8 eight times to load the write latches for the 32 instructions.		
<b>Step 10:</b> Unlock the NVMCON for programming.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 11:</b> Initiate the programming cycle.		
0000	A8E761	BSET NVMCON, #15
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #15
0000	000000	NOP
0000	000000	NOP
<b>Step 12:</b> Reset the device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 13:</b> Repeat Steps 7-12 until all 23 rows of executive memory are programmed.		

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## 12.2 Programming Verification

After the programming executive has been programmed to executive memory using ICSP, it must be verified. Verification is performed by reading out the contents of executive memory and comparing it with the image of the programming executive stored in the programmer.

Reading the contents of executive memory can be performed using the same technique described in [Section 11.10 “Reading Code Memory”](#). A procedure for reading executive memory is shown in [Table 12-2](#). Note that in Step 2, the TBLPAG register is set to 0x80 such that executive memory may be read.

**TABLE 12-2: READING EXECUTIVE MEMORY**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.</b>		
0000	200800	MOV #0x80, W0
0000	880190	MOV W0, TBLPAG
0000	EB0300	CLR W6
<b>Step 3: Initialize the write pointer (W7), and store the next four locations of executive memory to W0:W5.</b>		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP

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**TABLE 13-1: AC/DC CHARACTERISTICS (CONTINUED)**

AC/DC CHARACTERISTICS			Standard Operating Conditions (unless otherwise stated) Operating Temperature: 25° C is recommended			
Param. No.	Sym	Characteristic	Min	Max	Units	Conditions
P9b	TDLY5	Delay between PGD ↓ by programming executive to PGD released by programming executive	15	—	μs	—
P10	TDLY6	Delay between PGD released by programming executive to first PGC ↑ of response	5	—	μs	—
P11	TDLY7	Delay between clocking out response words	10	—	μs	—
P12a	TPROG	Row Programming cycle time	1	4	ms	ICSP mode
P12b	TPROG	Row Programming cycle time	0.8	2.6	ms	Enhanced ICSP mode
P13a	TERA	Bulk/Row Erase cycle time	1	4	ms	ICSP mode
P13b	TERA	Bulk/Row Erase cycle time	0.8	2.6	ms	Enhanced ICSP mode

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## APPENDIX B: HEX FILE FORMAT

Flash programmers process the standard HEX format used by the Microchip development tools. The format supported is the Intel® HEX 32 Format (INHX32). Please refer to Appendix A in the “*MPASM User's Guide*” (DS33014) for more information about hex file formats.

The basic format of the hex file is:

```
:BBAAAATTTHHHH...HHHHCC
```

Each data record begins with a 9-character prefix and always ends with a 2-character checksum. All records begin with ':' regardless of the format. The individual elements are described below.

- **BB** - is a two-digit hexadecimal byte count representing the number of data bytes that appear on the line. Divide this number by two to get the number of words per line.
- **AAAA** - is a four-digit hexadecimal address representing the starting address of the data record. Format is high byte first followed by low byte. The address is doubled because this format only supports 8-bits. Divide the value by two to find the real device address.
- **TT** - is a two-digit record type that will be '00' for data records, '01' for end-of-file records and '04' for extended-address record.
- **HHHH** - is a four-digit hexadecimal data word. Format is low byte followed by high byte. There will be  $BB/2$  data words following **TT**.
- **CC** - is a two-digit hexadecimal checksum that is the two's complement of the sum of all the preceding bytes in the line record.

Because the Intel hex file format is byte-oriented, and the 16-bit program counter is not, program memory sections require special treatment. Each 24-bit program word is extended to 32 bits by inserting a so-called “phantom byte”. Each program memory address is multiplied by 2 to yield a byte address.

As an example, a section that is located at 0x100 in program memory will be represented in the hex file as 0x200.

The hex file will be produced with the following contents:

```
:020000040000fa
:040200003322110096
:00000001FF
```

Notice that the data record (line 2) has a load address of 0200, while the source code specified address 0x100. Note also that the data is represented in “little-endian” format, meaning the Least Significant Byte (LSB) appears first. The phantom byte appears last, just before the checksum.



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